



NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MLN1037F** is Designed for

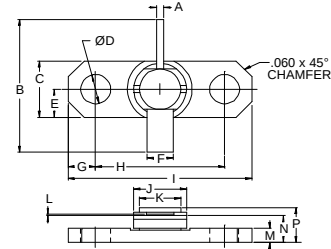
FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ $T_C = 25\text{ }^{\circ}\text{C}$
T_J	$-65\text{ }^{\circ}\text{C}$ to $+200\text{ }^{\circ}\text{C}$
T_{STG}	$-65\text{ }^{\circ}\text{C}$ to $+150\text{ }^{\circ}\text{C}$
θ_{JC}	$5.5\text{ }^{\circ}\text{C/W}$

PACKAGE STYLE .250 2L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E	.125 / 3.18	
F	.110 / 2.79	.117 / 2.97
G	.117 / 2.97	
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

ORDER CODE: ASI10628

CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50\text{ mA}$	35			V
BV_{CER}	$I_C = 50\text{ mA}$ $R_{BE} = 10\text{ }\Omega$	60			V
BV_{EBO}	$I_E = 10\text{ mA}$	4.0			V
I_{CES}	$V_E = 28\text{ V}$			5	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	10		100	---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			15	pF
P_{GE}	$V_{CE} = 20\text{ V}$ $I_{CQ} = 800\text{ mA}$ $f = 1.0\text{ GHz}$ $P_{OUT} = 5.0\text{ W}$	10			dB